

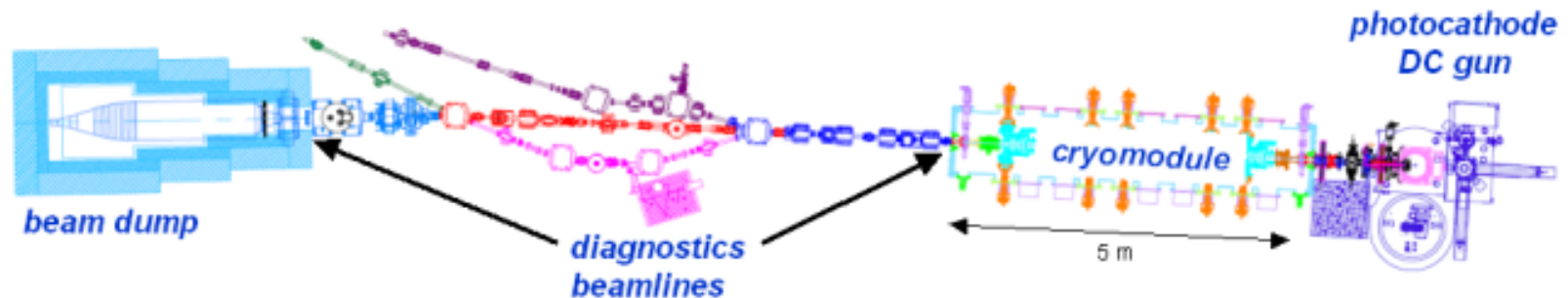


Spectral Response of GaAs (Cs, NF₃) Photocathodes

Teresa Esposito

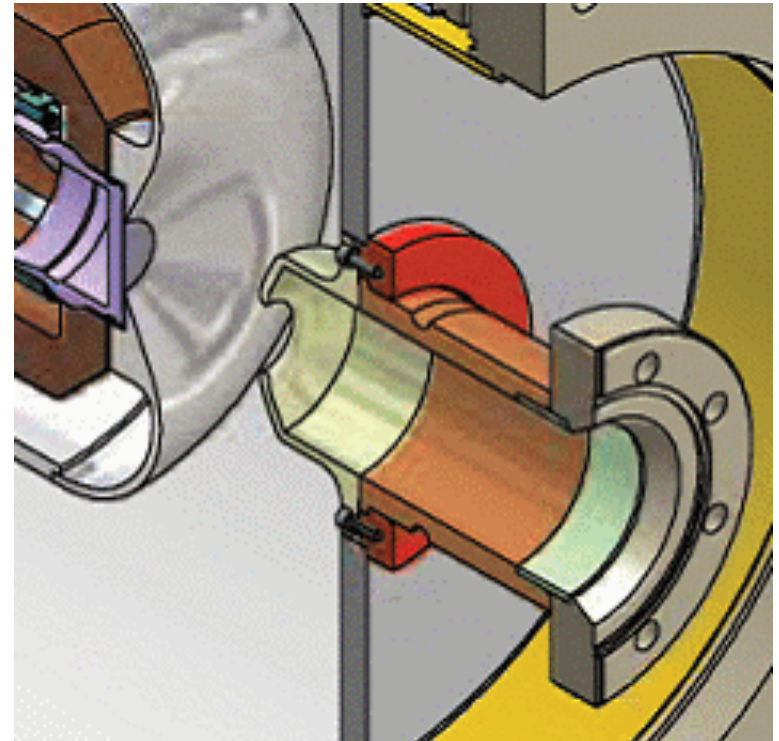
Mentors: I. Bazarov, L. Cultrera, S. Karkare

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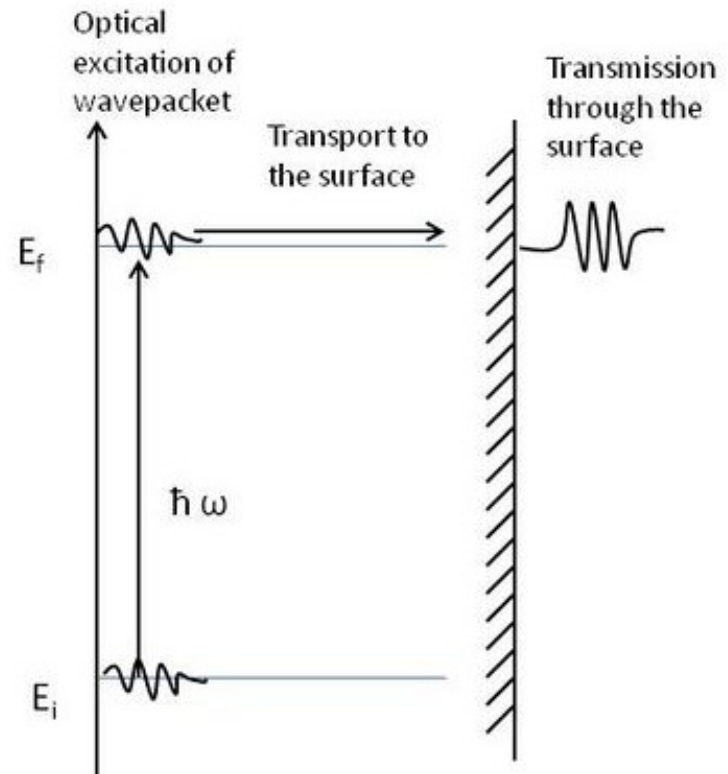


- Photocathode is used in ERL gun
- A laser pulse will trigger an electron bunch to be released
- Able to make electron bunches that are ideal for the ERL
 - High Quantum Efficiency
 - Low Mean Transverse Energy
 - Short time response

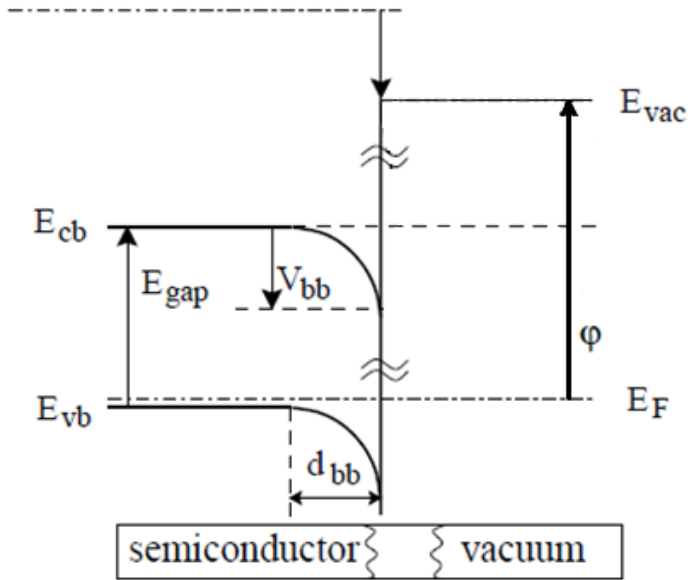


- 1) Photon absorption by an electron causing excitation from valence band to conduction band
- 2) Diffusion of electrons to the surface
- 3) Electrons escape from the bulk to the vacuum

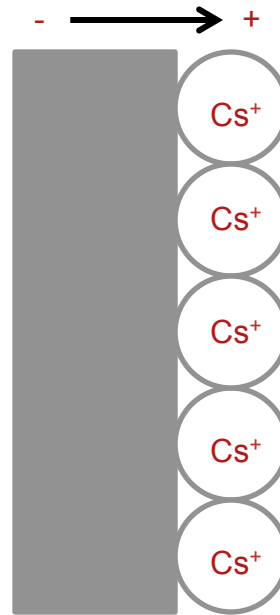
THREE STEP MODEL



Before Activation

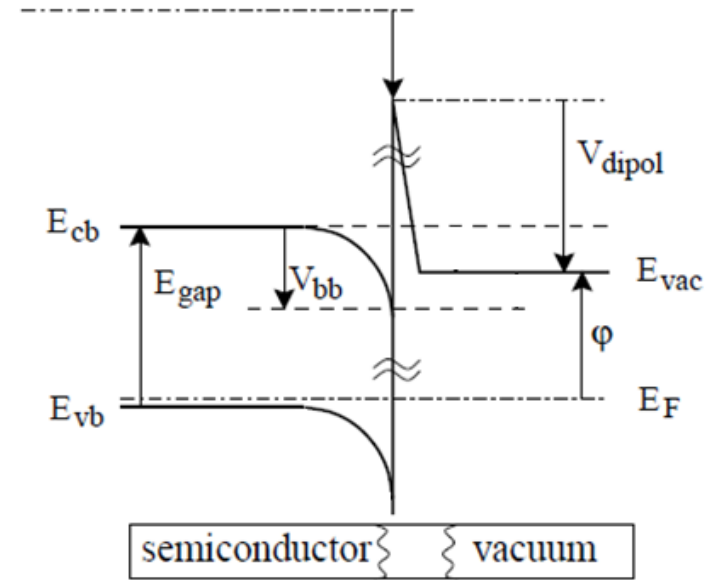


Electric field (V_{dipole})



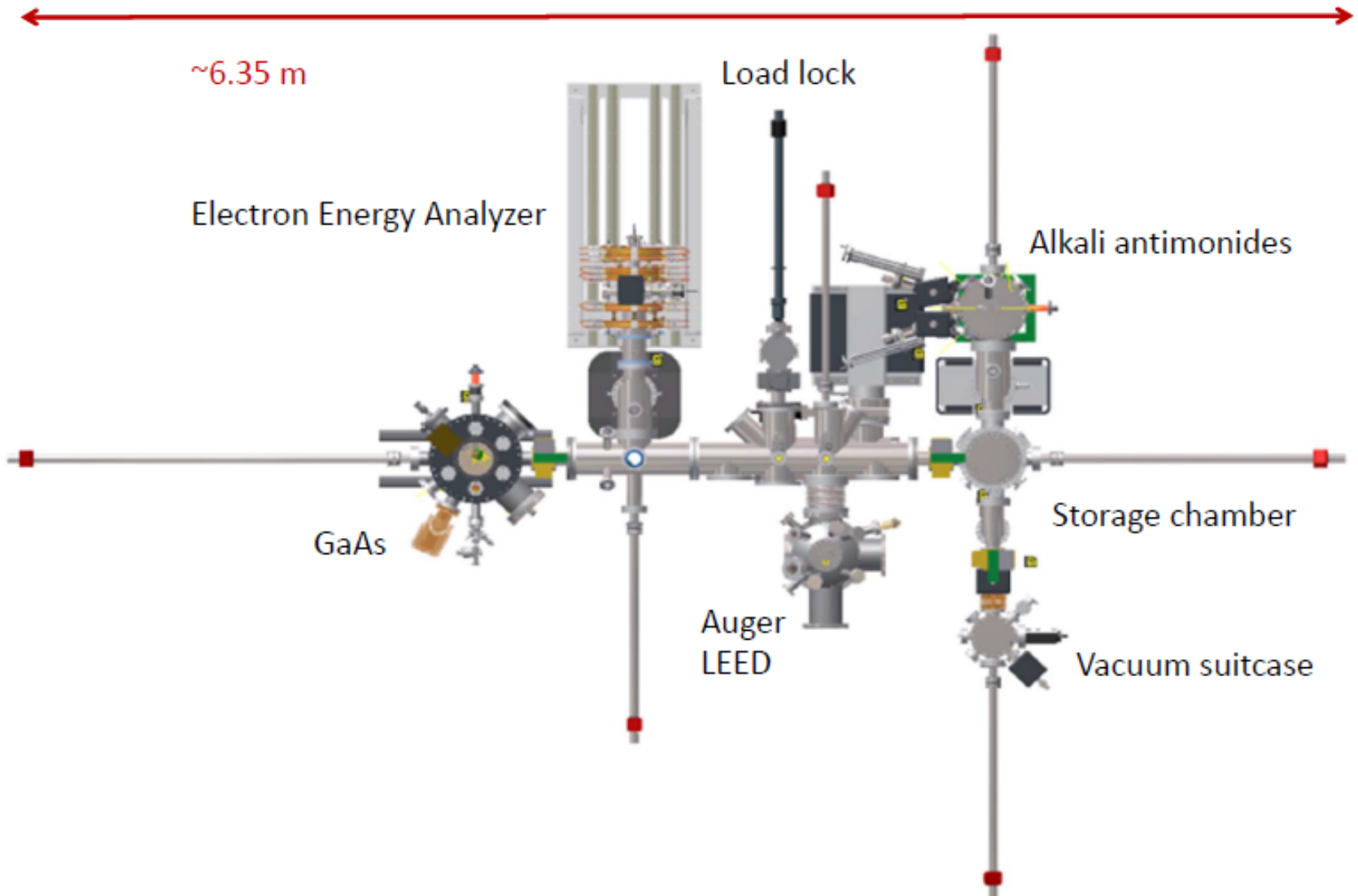
GaAs

After Activation (NEA)





- Study Process of Photoemission





- Number of emitted electrons per incident photon
 - Shine a 532nm laser onto the surface of the cathode
 - Causes photoemission and creates a current
 - Current is measured using a picoammeter
 - Use laser power (L_p) and photocurrent (P_c) to calculate QE

$$QE = P_c * h * c / L_p * e * \lambda$$

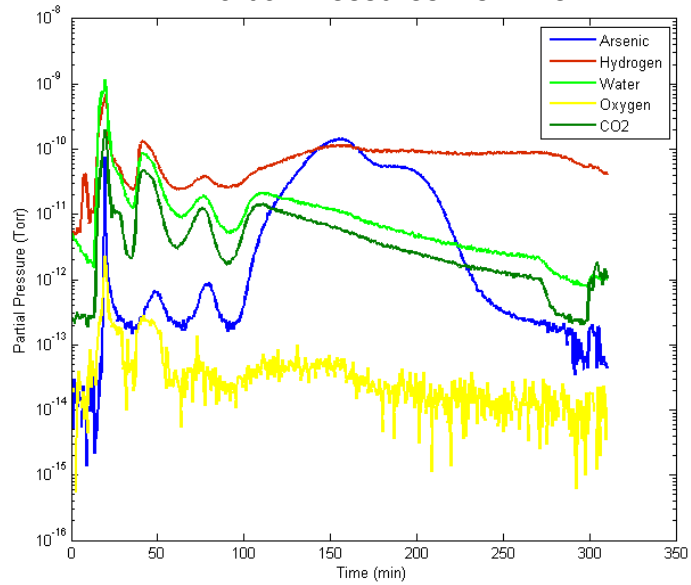


- **Sample 1:**
 - P-doped with Zn, doping level 6.3×10^{18} and 1.9×10^{19} holes/cm³
 - Cleaned with Acetone, Trichloroethylene and Anodized
 - Heated to 650°C under vacuum
- **Sample 2:**
 - GaAs grown by molecular beam epitaxy under UHV
 - Top 1000nm p-doped with C, doping level 2.0×10^{18} holes/cm³
 - Covered with As Cap to protect from air
 - Heated to 300°C under vacuum

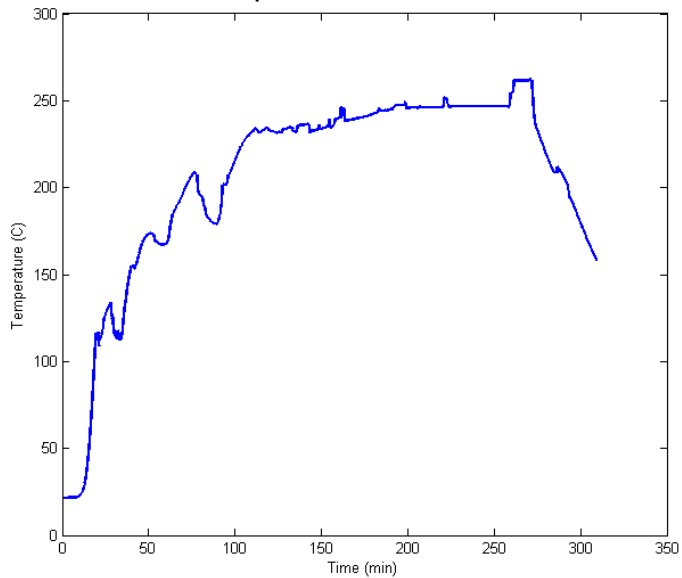


As Cap Removal

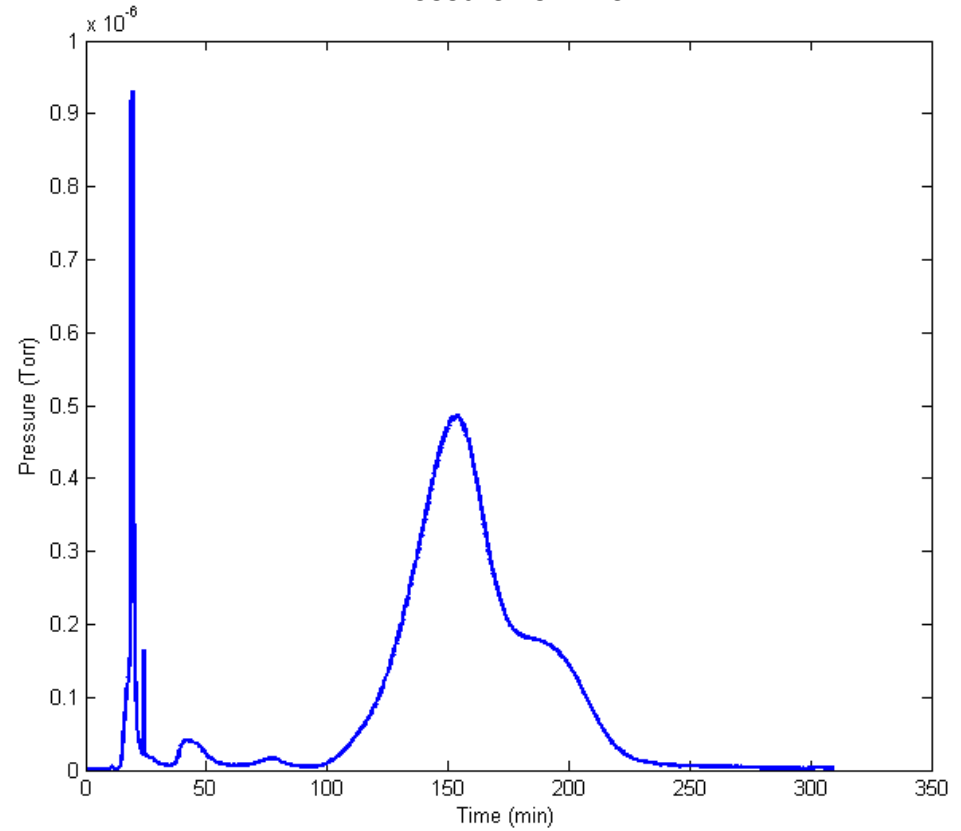
Partial Pressures vs Time



Temperature vs Time

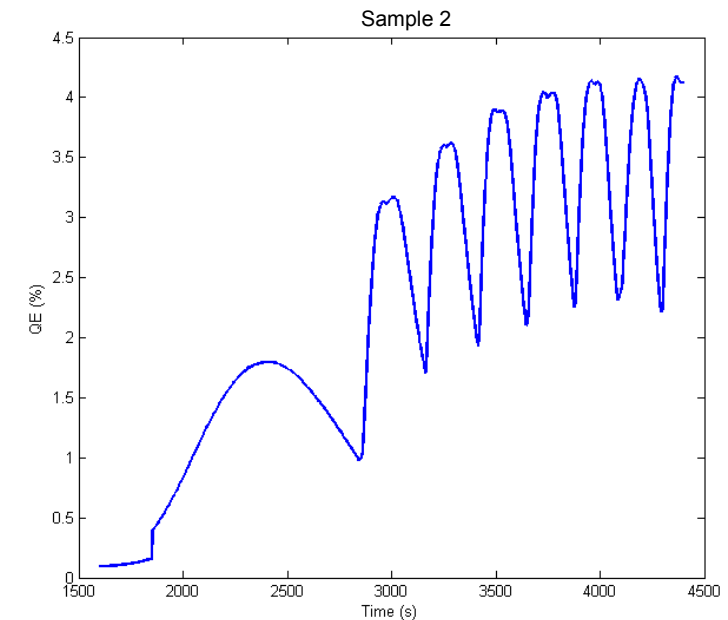
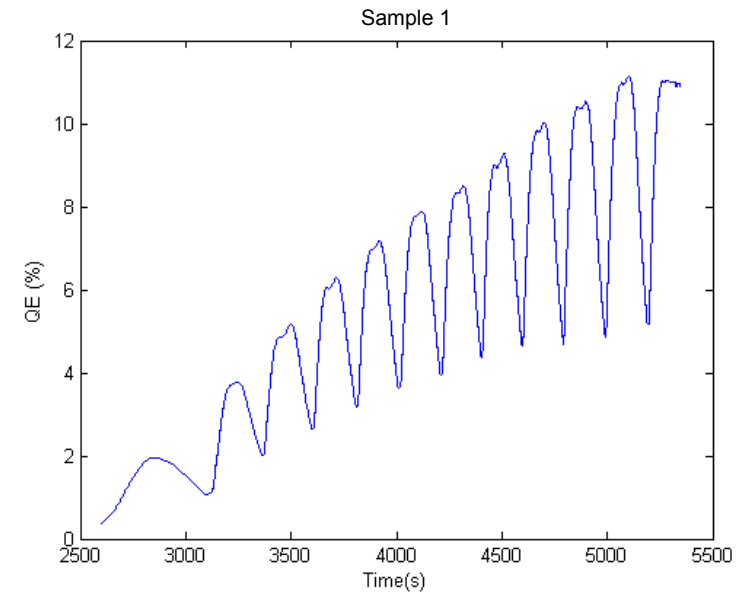


Pressure vs Time



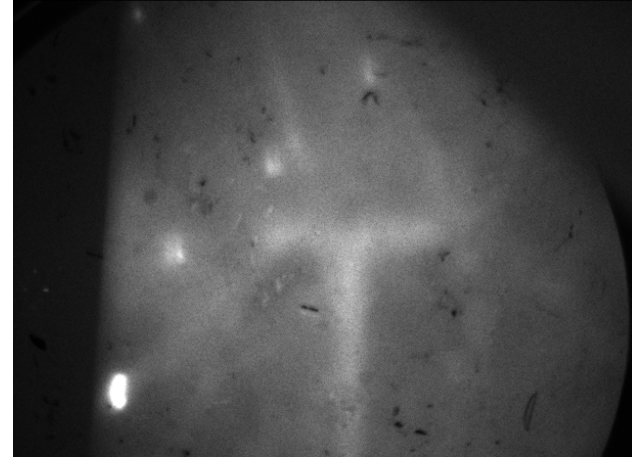
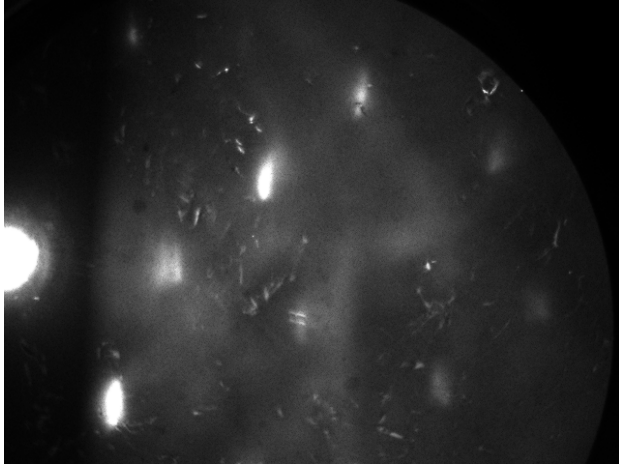


- Yo-yo activation
- Sample 1
 - Consistent activation to 10% QE
 - 1/e Lifetime ~80 hours
- Sample 2
 - Activation to 4.2% QE
 - 1/e Lifetime ~25 hours

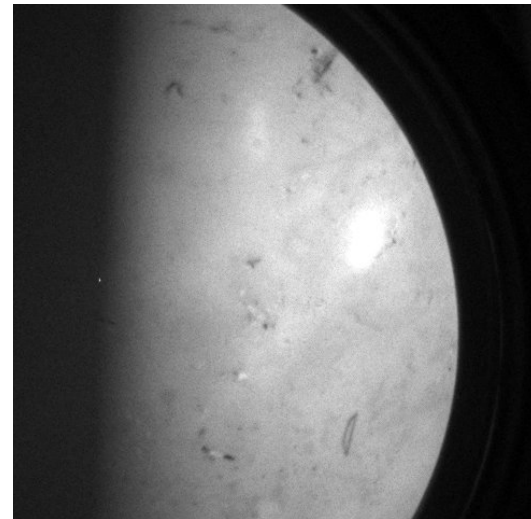
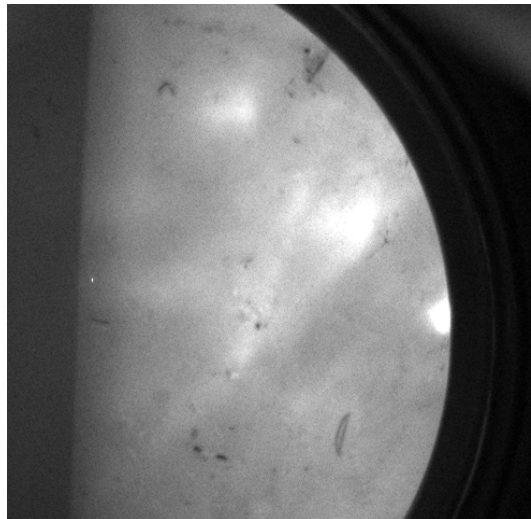




- Sample 1 Before and After (same position)

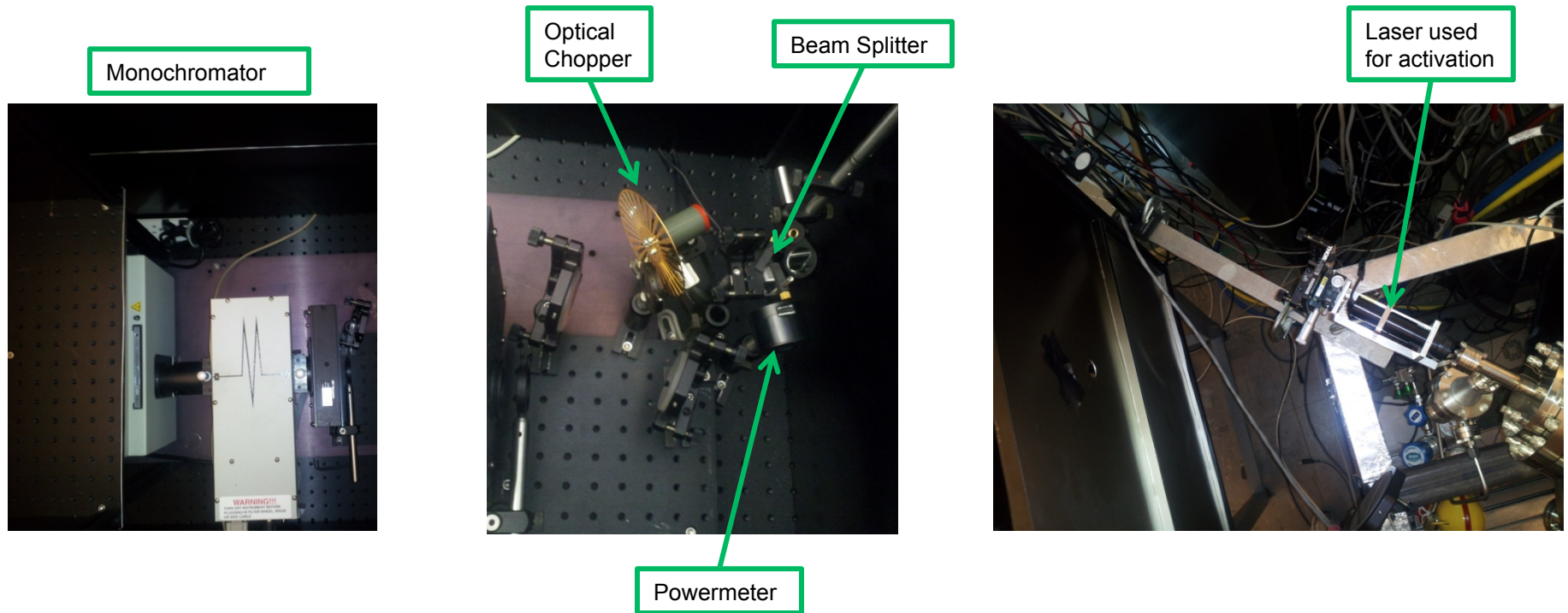


- Sample 2 Before and After



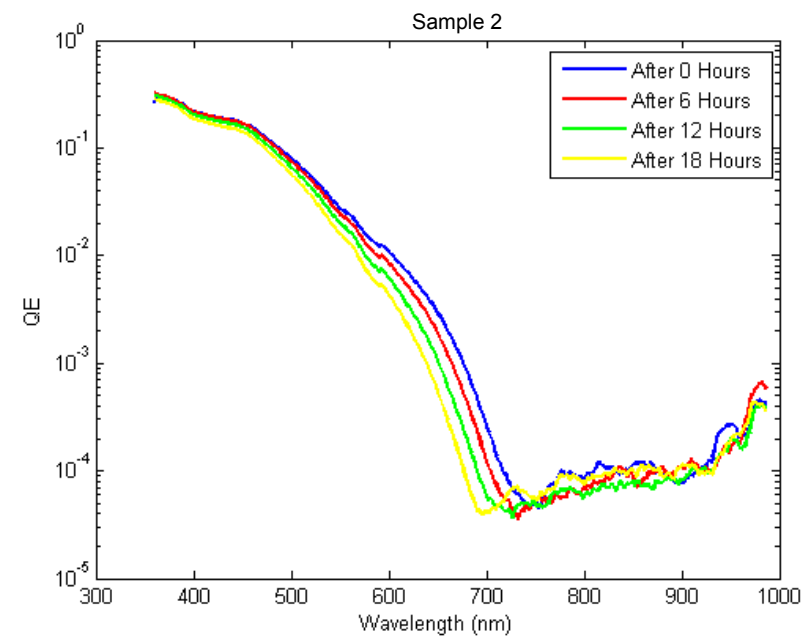
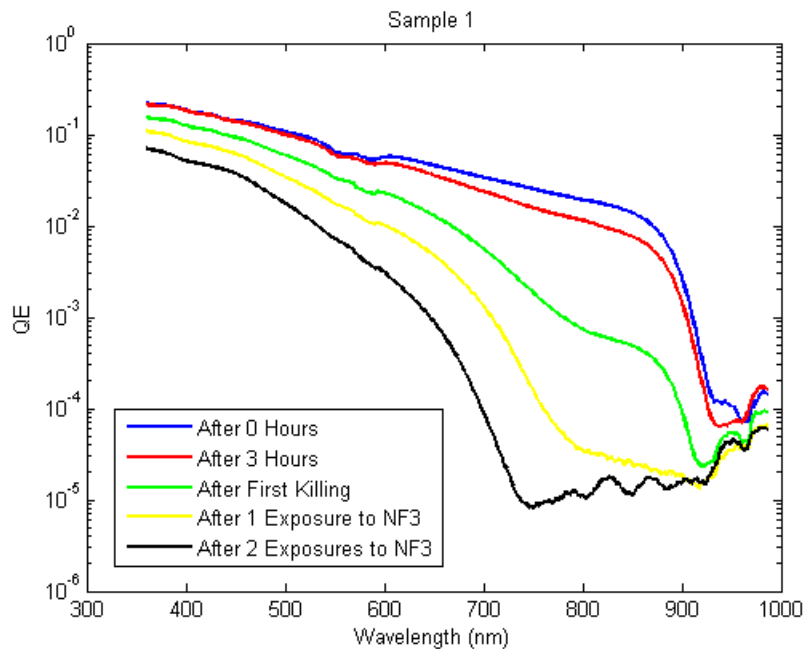


- Measure QE as a function of wavelength
- After the cathode is activated, QE is measured using a monochromator instead of a laser
- Isolates out one wavelength of light

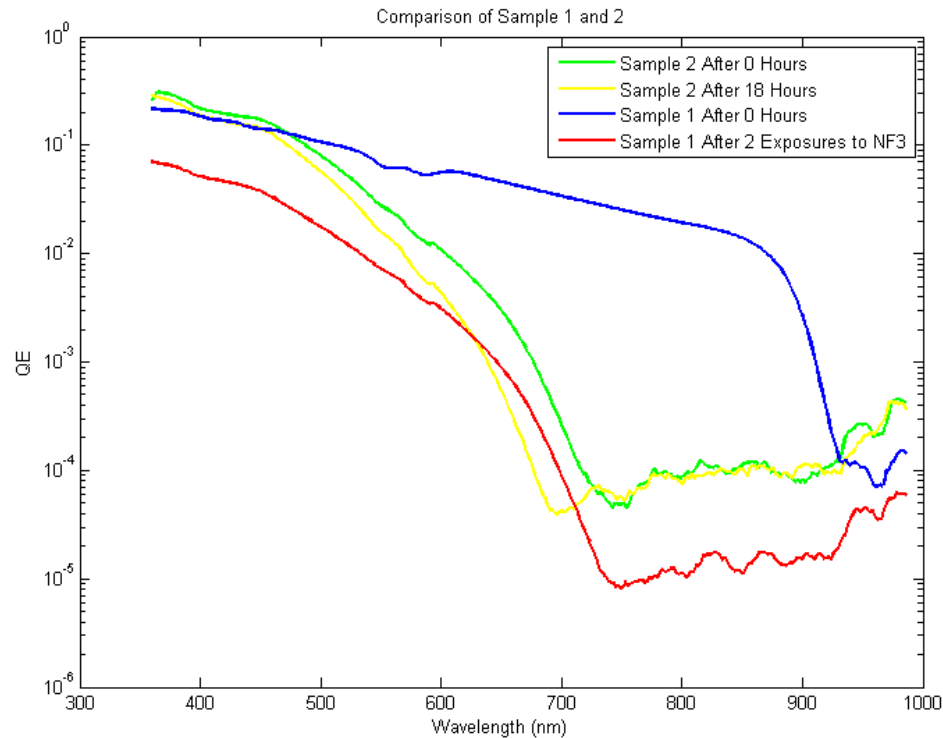




Spectral Response on Sample 1 & 2



- Continued measurements as cathode dies
- Band gap=1.33 eV (~900nm)
- Beyond band gap nothing gets excited
- When vacuum level is higher, even the excited electrons can't escape

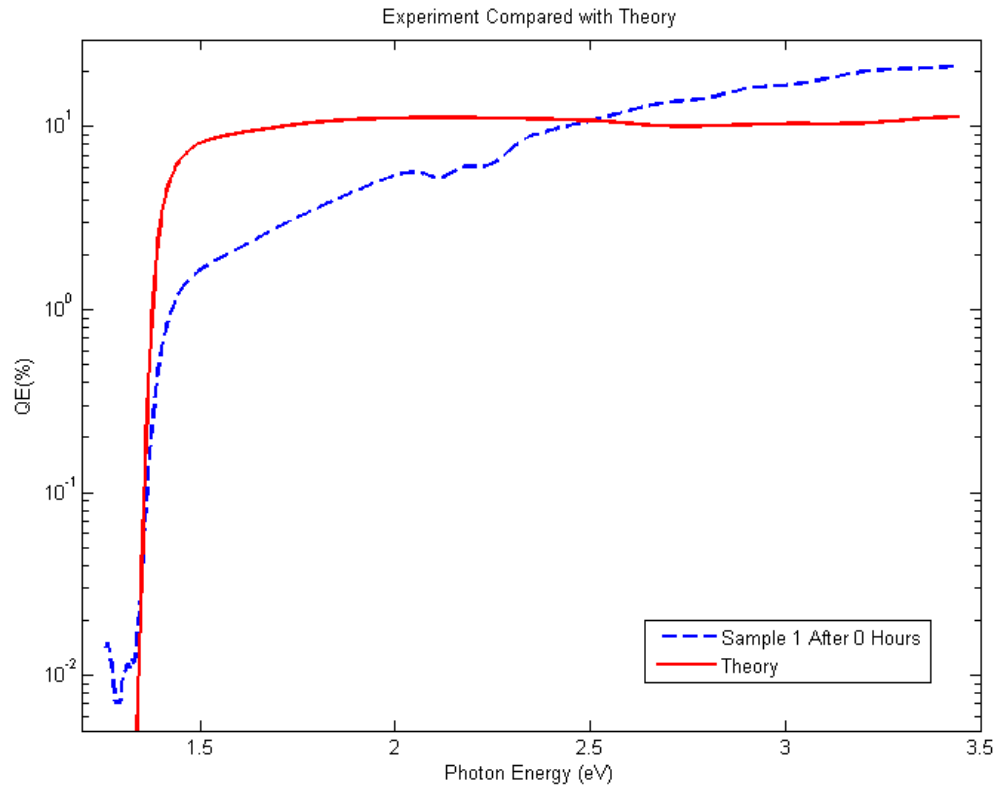


- Sample 2 behaves as Sample 1 after partial killing: may have never reached NEA
- Barrier is higher on Sample 2



$$QE(hf) = B[1 - R(hf)] / (1 + 1/\alpha(hf)L)$$

- QE can be calculated by modeling diffusion of electrons in GaAs
- Start and stay in a thermalized distribution
- GaAs properties
 - $R(hf)$ =optical reflectivity
 - $\alpha(hf)$ =optical absorption coefficient
 - L =electron diffusion length (1.6 μ m)
- Surface Properties
 - B =Surface escape probability



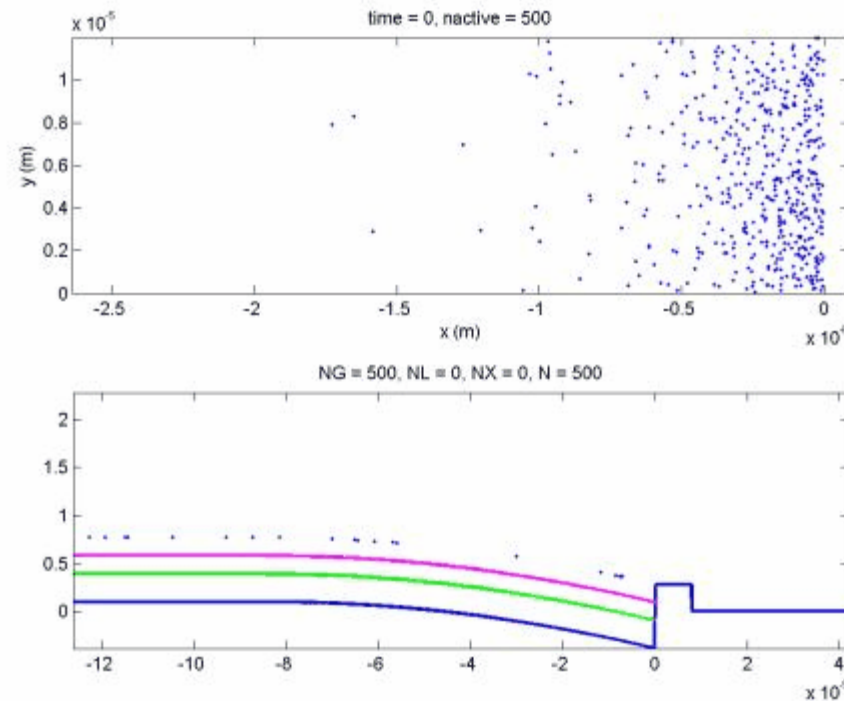
B=20%

- Drawbacks of theory
 - Does not explain band bending, barrier, scattering...



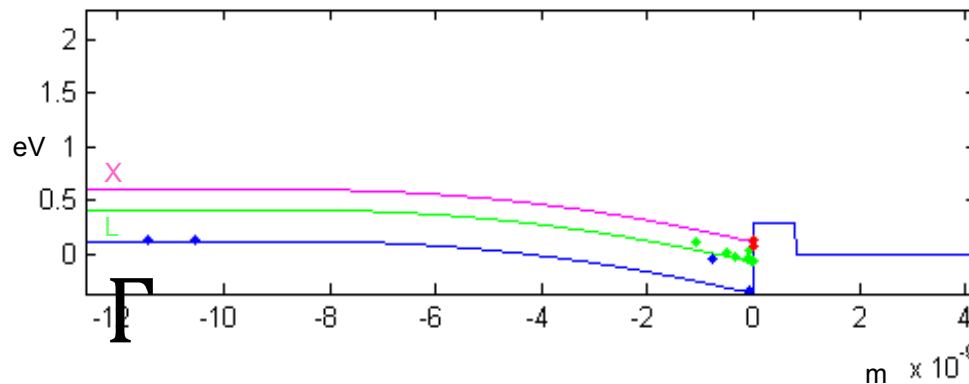
Monte Carlo Simulations

- Begin with electrons in a distribution caused by laser penetration
- Simulates the behavior of electrons in activated GaAs cathodes and tracks their position



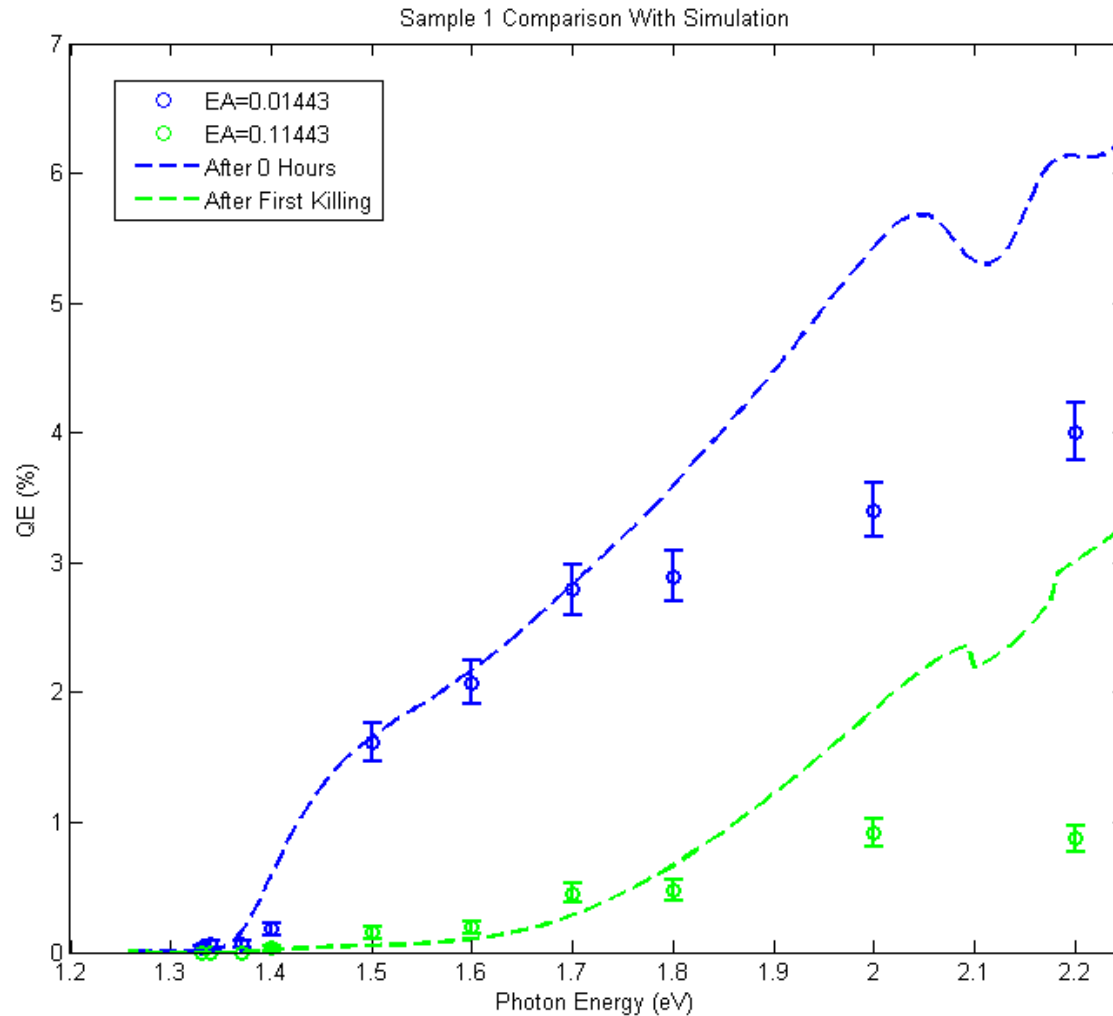


- We can run the code multiple times changing various parameters
- QE vs Incident Photon Energy
 - Can compare to experiment from spectral response
- Also changed was Surface Barrier height
 - Maximum Barrier= 0.28eV above Surface Barrier
 - Barrier Width= 0.8 nm





- Doping level = 1.0×10^{19}





- RHEED: after activation, the pattern gets more diffused
- Sample 1 has a smaller surface barrier than sample 2
- Sample 2 never reached negative affinity
- Monte Carlo simulations explain the experiment until about 1.8eV, so more work must be done to improve the code



Acknowledgements

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